Analog Power AM20N10-250DE MOSFET Datasheet

http://www.manuallib.com/analog-power/am20n10-250de-mosfet-datasheet.html

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low rDS(on) and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, and cordless telephones.

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Analog Power

AM20N10-250DE

N-Channel 100-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low r_{DS(on)} provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe DPAK saves board space
- Fast switching speed
- High performance trench technology

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V_{DS} (V)

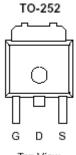
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PRODUCT SUMMARY

 $r_{DS(on)} m(\Omega)$

 $280 @ V_{CS} = 10V$

 $355 @V_{CS} = 4.5V$



 $\mathbf{I}_{\mathbf{D}}(\mathbf{A})$

11

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Top View

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage		V _{DS}	100	v		
Cate-Source Voltage		V _{GS}	±2 0			
Continuous Drain Current ^a	$T_{C}=25^{\circ}C$	I _D	11			
Pulsed Drain Current ^b		I _{DM}	36	A		
Continuous Source Current (Diode Conduction) ^a		Is	30	Α		
Power Dissipation ^a	$T_{C}=25^{\circ}C$	P _D	50	W		
Operating Junction and Storage Temperature Range		TJ, Tstg	-55 to 175	°C		

2000V

THERMAL RESISTANCE RATINGS						
Parameter	er Symbol Maximum		Units			
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	50	°C/W			
Maximum Junction-to-Case	$R_{\theta JC}$	3.0	°C/W			

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

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Parame te r	Chal	Test Conditions	Limits			T Tania
	Symbol		Min	Тур	Max	Unit
Static						
Gate-Threshold Voltage	VGS(th)	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1.0			V
Gate-Body Leakage	Igss	$V_{DS} = 0 V, V_{GS} = 20 V$			±10	μA
Zero Gate Voltage Drain Current	In an	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
	I _{DSS}	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			25	
On-State Drain Current ^A	I _{D(on)}	$V_{DS} = 5 V, V_{GS} = 10 V$	34			А
Drain-Source On-Resistance ^A		$V_{GS} = 10 \text{ V}, I_D = 4.5 \text{ A}$			280	mΩ
	rDS(on)	$V_{GS} = 4.5 \text{ V}, I_D = 4 \text{ A}$			355	
Forward Tranconductance ^A	g _{fs}	$V_{DS} = 15 \text{ V}, I_D = 4.5 \text{ A}$		5		S
Diode Forward Voltage	Vsd	$I_S = 9 A$, $V_{GS} = 0 V$		1		V
Dynamic ^b						
Total Gate Charge	Qg	$V_{DS} = 50 \text{ V}, V_{GS} = 5.5 \text{ V},$ $I_D = 4.5 \text{ A}$		10		nC
Gate-Source Charge	Qgs			2		
Gate-Drain Charge	Qgd			7.8		
Turn-On Delay Time	td(on)	$V_{\rm DD} = 50 \ V, R_{\rm L} = 11.1 \ \Omega \ ,$ $I_{\rm D} = 4.5 \ A, \qquad V_{\rm GEN} = 10 \ V$		4.8		nS
Rise Time	tr			4		
Turn-Off Delay Time	td(off)			12.8		
Fall-Time	tf			4		

Notes

- a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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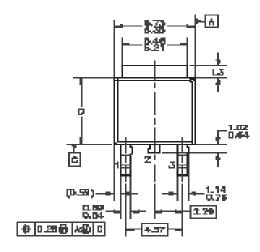
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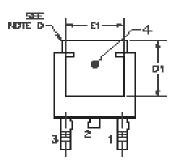
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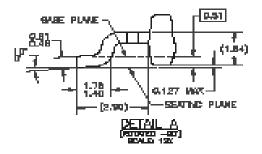
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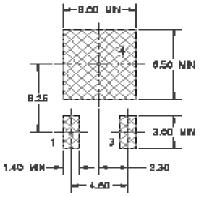
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Package Information

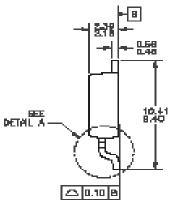








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